TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC1815

Audio Frequency General Purpose Amplifier Applications Driver Stage Amplifier Applications

• High voltage and high current:  $V_{CEO} = 50 V (min)$ ,

IC = 150 mA (max)

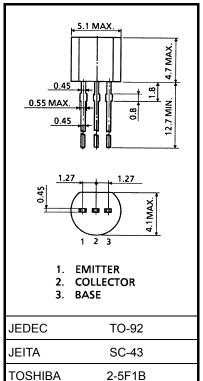
• Excellent hFE linearity: hFE (2) = 100 (typ.)

at VCE = 6 V, IC = 150 mA : hFE (IC = 0.1 mA)/hFE (IC = 2 mA)

- = 0.95 (typ.)
- Low noise: NF = 1dB (typ.) at f = 1 kHz
- Complementary to 2SA1015 (O, Y, GR class)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V <sub>CBO</sub>	60	V	
Collector-emitter voltage	V <sub>CEO</sub>	50	V	
Emitter-base voltage	V <sub>EBO</sub>	5	V	
Collector current	Ι <sub>C</sub>	150	mA	
Base current	Ι <sub>Β</sub>	50	mA	
Collector power dissipation	P <sub>C</sub>	400	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	



Weight: 0.21 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$	_		0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 5 \text{ V}, \text{ I}_{C} = 0$	_	—	0.1	μA
DC current gain	h <sub>FE (1)</sub> (Note)	$V_{CE} = 6 \text{ V}, \text{ I}_{C} = 2 \text{ mA}$	70	_	700	
	h <sub>FE (2)</sub>	$V_{CE} = 6 \text{ V}, \text{ I}_{C} = 150 \text{ mA}$	25	100	—	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$		0.1	0.25	V
Base-emitter saturation voltage	V <sub>BE (sat)</sub>	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$		—	1.0	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$	80	_	_	MHz
Collector output capacitance	Cob	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	2.0	3.5	pF
Base intrinsic resistance	r <sub>bb'</sub>	V <sub>CE</sub> = 10 V, I <sub>E</sub> = -1 mA f = 30 MHz		50	_	Ω
Noise figure	NF	$V_{CE}$ = 6 V, I <sub>C</sub> = 0.1 mA f = 1 kHz, R <sub>G</sub> = 10 k $\Omega$		1.0	10	dB

Note: hFE classification O: 70~140, Y: 120~240, GR: 200~400, BL: 350~700

Unit: mm

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1

0.3

0

0.4

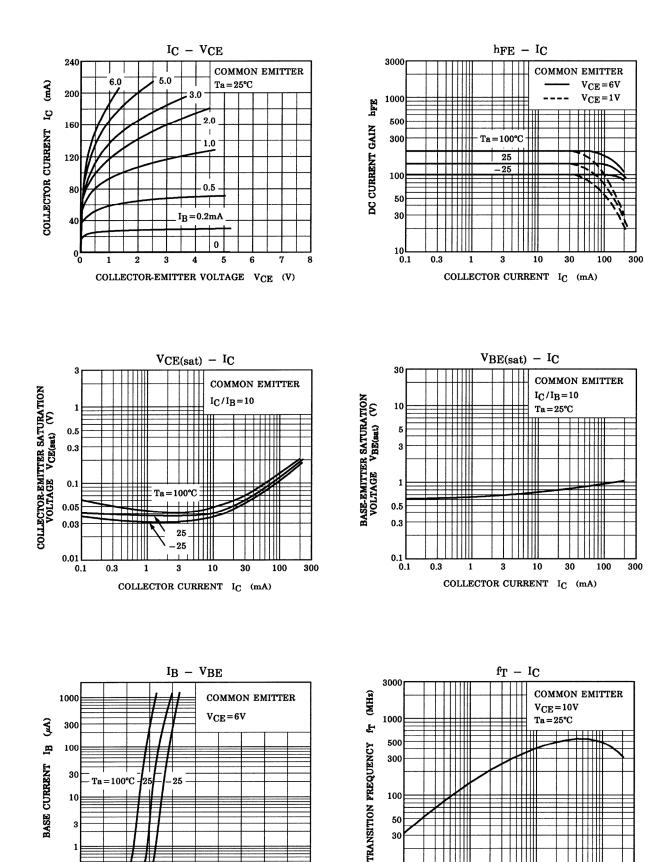
1.2

0.8

BASE-EMITTER VOLTAGE VBE (V)

1.6

2.0



300

10

0.1

0.3

3

EMITTER CURRENT IC (mA)

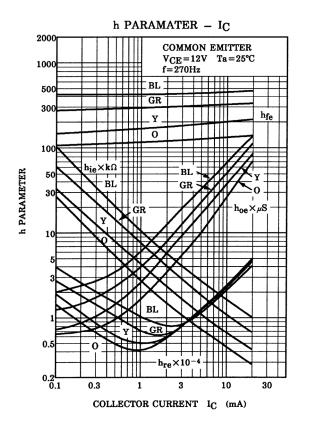
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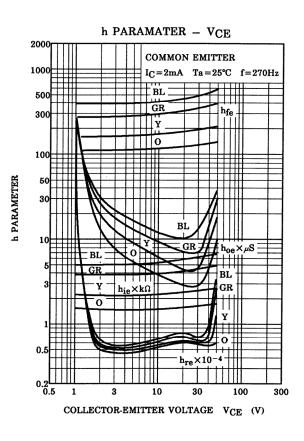
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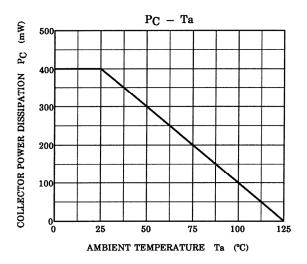
30

100

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